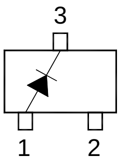
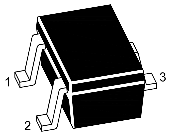
1SS370W

Silicon Epitaxial Planar Diodes

High Voltage Switching Diode

For high voltage and high speed switching applications





SOT-323 Plastic Package
Marking Code: **F5**

Absolute Maximum Ratings ($T_a = 25\ ^{\circ}C$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V_R	200	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (tp = 10 ms)	I_{FSM}	2	A
Power Dissipation	P_D	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25\ ^{\circ}C$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10$ mA at $I_F = 100$ mA	V_F V_F	1 1.2	V
Reverse Current at $V_R = 50$ V at $V_R = 200$ V	I_R I_R	0.1 1	µA
Total Capacitance at $V_R = 0$, f = 1 MHz	C_T	3	pF
Reverse Recovery Time at $I_F = 10$ mA	t_{rr}	60	ns

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Dated : 15/06/2009

Reverse Recovery Time (t_{rr}) Test Circuit